**Investigation of Morphology of Porous Silicon Formed on N+ Type Silicon**

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**Abstract.** The properties of porous silicon (PS) are closely connected to its morphology, much investigation has been done in order to correlate the morphological characteristics of PS with the anodisation parameters. In this paper the results of morphological analysis of PS formed on N+type substrates of 〈1 0 0〉 and 〈1 1 1〉 orientation are presented. The dependences of the porosity, thickness of PS, density of pores and of the effective surface on the current density are obtained. Interpretation of these results in terms of diffusion layer and energy levels is given, with special attention given to the low current density case.

**Keywords:** porous silicon, morphology, mechanism of growth.

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